

2N4428 (SILICON)

NPN SILICON RF POWER TRANSISTOR

... designed primarily for use in large signal VHF and UHF amplifier output stages in military and industrial communications applications.

- High Power Output –
 $P_{out} = 0.75$ Watt with 10 dB Gain @ $f = 500$ MHz
- High Current-Gain-Bandwidth Product –
 $f_T = 1000$ MHz (Typ) @ $I_C = 50$ mAdc
- Multiple Emitter Construction for Excellent High Frequency Performance

*MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	35	Vdc
Collector-Base Voltage	V_{CB}	55	Vdc
Emitter-Base Voltage	V_{EB}	3.5	Vdc
Collector Current – Continuous	I_C	425	mAdc
Base Current – Continuous	I_B	150	mAdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	3.5 20	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$

*Indicates JEDEC Registered Data.

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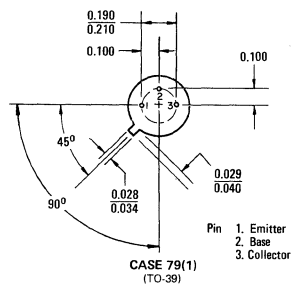
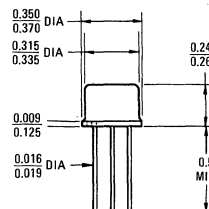
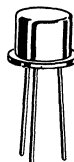
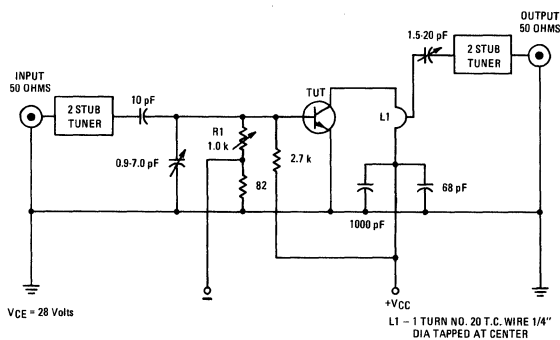


FIGURE 1 – 500 MHz TEST CIRCUIT



Adjust R1 for $I_C = 70$ mA with no RF Signal Applied

2N4428 (continued)

*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage ($I_C = 20 \text{ mAdc}$, $I_B = 0$)	$V_{CE0(sus)}$	35	—	—	Vdc
Collector-Emitter Sustaining Voltage ($I_C = 20 \text{ mAdc}$, $R_{BE} = 10 \text{ ohms}$)	$V_{CE R(sus)}$	55	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 55 \text{ Vdc}$, $V_{BE} = -1.5 \text{ Vdc}$)	I_{CEX}	—	—	1.0	mAdc
Emitter Cutoff Current ($V_{EB} = 3.5 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	—	—	0.1	mAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 50 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 400 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20 5.0	— —	200 —	—
DYNAMIC CHARACTERISTICS					
Current-Gain-Bandwidth Product ($I_C = 50 \text{ mAdc}$, $V_{CE} = 20 \text{ Vdc}$, $f = 200 \text{ MHz}$)	f_T	700	1000	—	MHz
Output Capacitance ($V_{CB} = 28 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{ob}	—	1.2	3.5	pF
FUNCTIONAL TEST					
Power Input (Figure 1) ($P_{out} = 750 \text{ mW}$, $V_{CE} = 28 \text{ Vdc}$, $R_S = 50 \text{ Ohms}$, $f = 500 \text{ MHz}$)	P_{in}	—	—	75	mW
Collector Efficiency (Figure 1) ($P_{out} = 750 \text{ mW}$, $V_{CE} = 28 \text{ Vdc}$, $R_S = 50 \text{ Ohms}$, $f = 500 \text{ MHz}$)	η	35	—	—	%

*Indicates JEDEC Registered Data.

FIGURE 2 – CURRENT-GAIN-BANDWIDTH PRODUCT

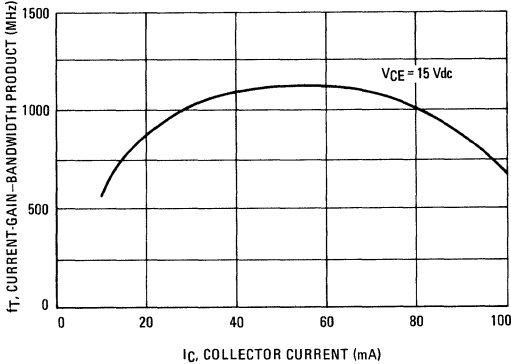


FIGURE 3 – OUTPUT POWER versus FREQUENCY

